

ESDU5V6P

SILICON EPITAXIAL PLANAR DIODE

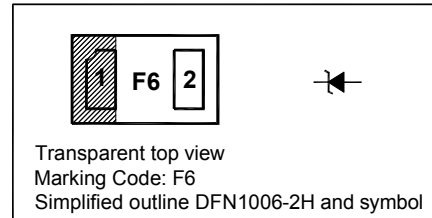
ESD protection diode

Features

- Ultra small mold type
- high reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

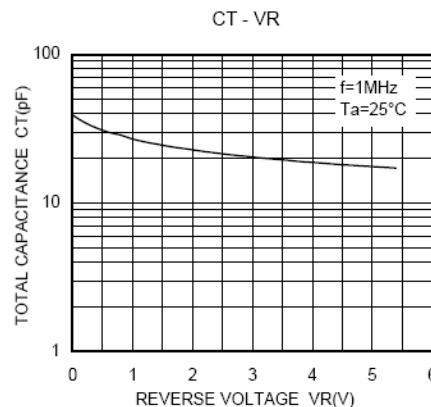
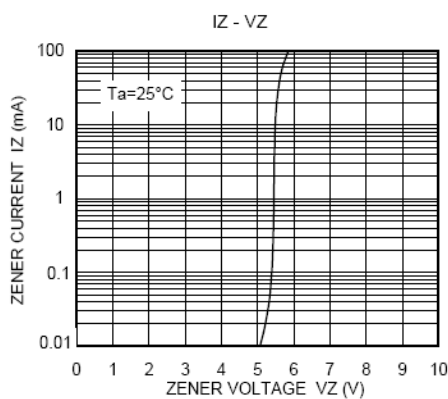


Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
IEC61000-4-2 (ESD) Contact	V _{ESD}	± 15	KV
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C
Operation Temperature Range	T _{opr}	- 55 to + 150	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Zener Voltage at I _Z = 5 mA	V _Z	5.3	-	6	V
Reverse Current at V _R = 3.5 V	I _R	-	-	1	µA
Dynamic Impedance at I _{ZT} = 5 mA	Z _{ZT}	-	-	30	Ω
Capacitance between Terminals at V _R = 0 V, f = 1 MHz	C _T	-	40	-	pF



TOP DYNAMIC



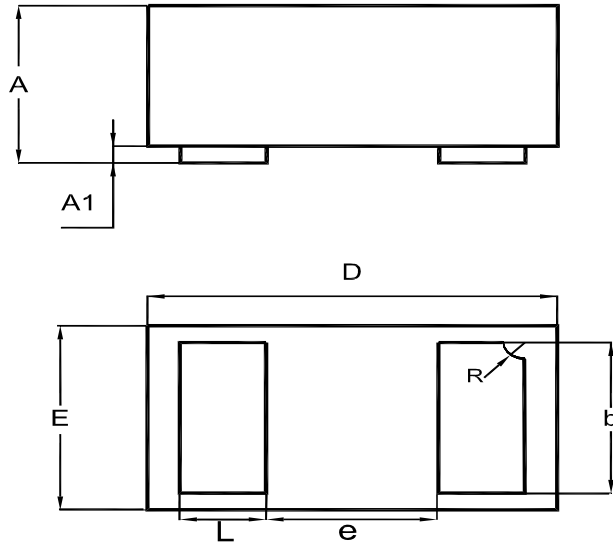
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PACKAGE OUTLINE

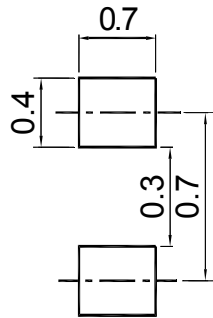
Plastic surface mounted package

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51 0.46	0.05 0	0.55 0.45	1.05 0.95	0.65 0.55	0.4	0.3 0.2	0.15 0.05

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2H	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

TOP DYNAMIC



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